

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







(Ta=25°C)

With built-in flywheel diode

Absolute maximum ratings

(12-23-6)							
Symbol	Ratings	Unit					
Vсво	-60	V					
VCEO	-60	V					
VEBO	-6	V					
Ic	-3	Α					
ICP	-6 (PW≤1ms, Du≤50%)	Α					
Ів	-0.5	Α					
lF	–6 (PW≤0.5ms, Du≤25%)	Α					
IFSM	-8 (PW≤10ms, Single pulse)	Α					
VR	100	V					
Рт	4 (Ta=25°C)	10/					
	20 (Tc=25°C)	W					
Tj	150	°C					
Tstg	-40 to +150	°C					

Electrical characteristics

Symbol	Specification			Hait	Conditions
	min	typ	max	Unit	Conditions
Ісво			-10	μΑ	Vcb=-60V
ІЕВО			-10	mA	VEB=-6V
VCEO	-60			٧	Ic=-10mA
hfE	2000	5000	12000		Vce=-4V, Ic=-2A
Vce(sat)			-1.5	٧	Ic=-2A, Iв=-4mA
V _{RE} (sat)			-2.0	V	

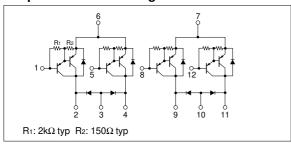
● Diode for flyback voltage absorption

(Ta=25°C)

(Ta=25°C)

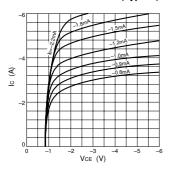
Symbol	Specification		l lmit	Conditions	
	min	typ	max	Unit	Conditions
VR	100			V	IR=10μA
VF			1.2	V	IF=1A
lr			10	μΑ	V _R =100V
trr		100		ns	I=±±100mA

■Equivalent circuit diagram

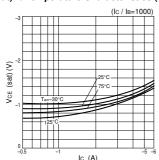


■ Characteristic curves

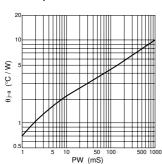
Ic-VcE Characteristics (Typical)



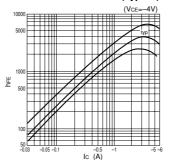
VcE(sat)-Ic Temperature Characteristics (Typical)



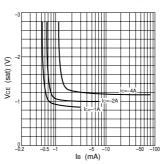
 $\theta_{\text{j-a-PW}}$ Characteristics



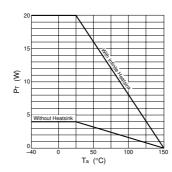
hfe-Ic Characteristics (Typical)



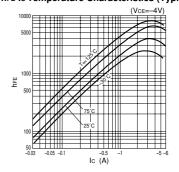
Vce(sat)-IB Characteristics (Typical)



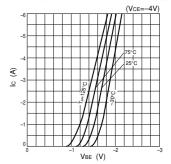
PT-Ta Characteristics



hfe-Ic Temperature Characteristics (Typical)



Ic-VBE Temperature Characteristics (Typical)



Safe Operating Area (SOA)

